ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089
http://www.nteinc.com

NTE326
Silicon P–Channel JFET Transistor
General Purpose AF Amplifier
TO92 Type Package

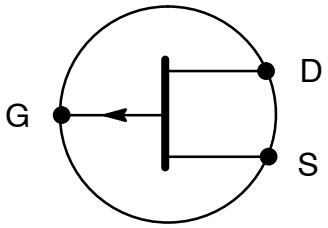
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

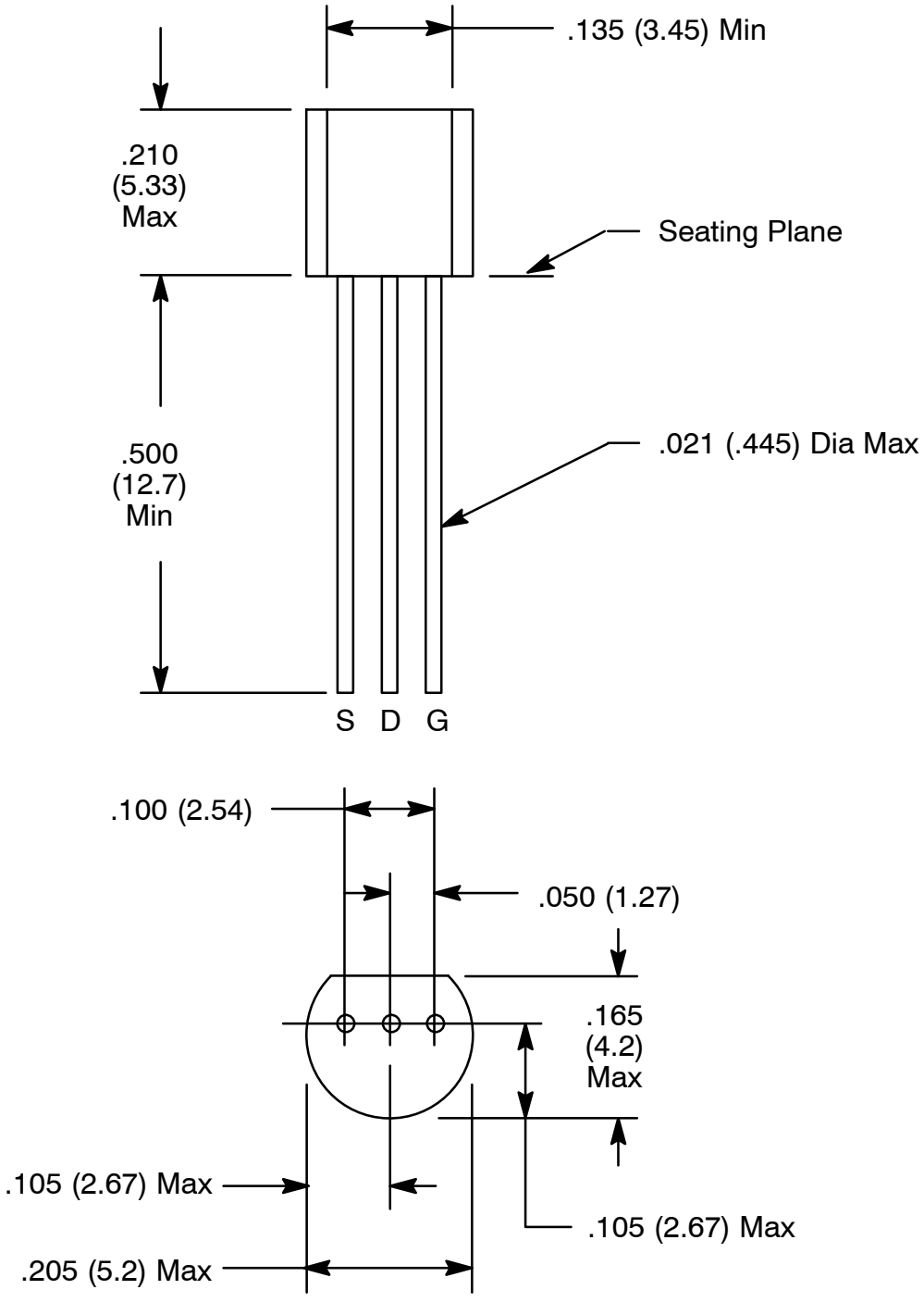
Drain–Gate Voltage, V_{DG} 40V
Reverse Gate–Source Voltage, V_{GSR} 40V
Forward Gate Current, $I_{G(f)}$ 10mA
Total Device Dissipation (T_A = +25°C), P_D 310mW
Derate Above 25°C . . . . . 2.82mW/°C
Operating Junction Temperature Range, T_J . . . . . –65° to +135°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Gate–Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = 10μA, V_{DS} = 0	40	–	–	V
Gate Reverse Current	I_{GSS}	V_{GS} = 20V, V_{DS} = 0	–	–	5	nA
		V_{GS} = 20V, V_{DS} = 0, T_A = +100°C	–	–	1	μA
Gate–Source Cutoff Voltage	$V_{GS(off)}$	I_D = 1μA, V_{DS} = 15V	1.0	–	7.5	V
Gate–Source Voltage	V_{GS}	I_D = 0.2mA, V_{DS} = 15V	0.8	–	4.5	V
ON Characteristics						
Zero–Gate–Voltage Drain Current	I_{DSS}	V_{DS} = 15V, V_{GS} = 0, f = 1kHz	2	–	9	mA
Small–Signal Characteristics						
Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = 15V, V_{GS} = 0, f = 1kHz	1500	–	5000	μmho
Output Admittance	$\|y_{os}\|$	V_{DS} = 15V, V_{GS} = 0, f = 1kHz	–	–	75	μmho
Input Capacitance	C_{iss}	V_{DS} = 15V, V_{GS} = 0, f = 1MHz	–	5	7	pF
Reverse Transfer Capacitance	C_{rss}	V_{DS} = 15V, V_{GS} = 0, f = 1MHz	–	1	2	pF
Functional Characteristics						
Noise Figure	NF	V_{DS} = 15V, V_{GS} = 0, R_G = 1MΩ, f = 100Hz, BW = 1Hz	–	1.0	2.5	dB
Equivalent Short–Circuit Input Noise Voltage	e_n	V_{DS} = 15V, V_{GS} = 0, f = 100Hz, BW = 1Hz	–	60	115	$nV/\sqrt{Hz}$

Rev. 2–16


G
D
S


.135 (3.45) Min
.210
(5.33)
Max
Seating Plane
.500
(12.7)
Min
.021 (.445) Dia Max
S D G
.100 (2.54)
.050 (1.27)
.165
(4.2)
Max
.105 (2.67) Max
.105 (2.67) Max
.205 (5.2) Max